

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-5. (canceled)

6 (new): An interposer-forming clad plate for use in a semiconductor device manufactured by press-bonding a copper foil material and a nickel foil material at a rolling reduction of 0.1 to 3%.

7 (new): An interposer-forming clad plate for use in a semiconductor device manufactured by press-bonding a copper foil material having nickel plating on one surface or both surfaces and other copper foil material or a copper foil material having nickel plating on one surface at a rolling reduction of 0.1 to 3%.

6 (new): A method of manufacturing an interposer-forming clad layer for use in a semiconductor device as defined in any one of claims 1 or 2 wherein the interposer-forming clad plate for use in the semiconductor device is formed by previously applying an activating treatment to the bonded surfaces of the copper foil and the nickel foil or nickel plating in a vacuum vessel and then laminating the copper foil and the nickel foil material or nickel plating and cold press-bonding them at a rolling reduction of 0.1 to 3% in

which the activating treatment is applied in an inert gas atmosphere at an extremely low pressure of 1×10^1 to 1×10^{-2} Pa, using the nickel plated copper foil material and the copper foil material as one electrode A having the bonding surfaces grounded to the earth, respectively, and conducting glow discharge by applying an AC current at 1 to 50 MHz between it and the other electrode B supported insulatively and applying sputter etching, with the area of the electrode exposed in plasmas caused by the glow discharge being $1/3$ or less of the electrode B.